BSS123LT1G, BVSS123LT1G

Power MOSFET 170 mAmps, 100 Volts

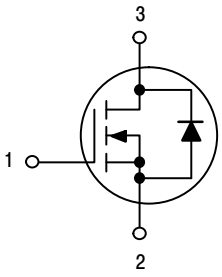
N−Channel SOT−23

ON Semiconductor®

www.onsemi.com

170 mAMPS
100 VOLTS
$R_{DS(on)}$ = 6 Ω

N−Channel



Features

- BVSS Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC−Q101 Qualified and PPAP Capable
- These Devices are Pb−Free and are RoHS Compliant

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Drain−Source Voltage	V_{DSS}	100	Vdc
Gate−Source Voltage − Continuous − Non−repetitive ($t_p \le 50$ μs)	 V_{GS} V_{GSM}	 ±20 ±40	 Vdc Vpk
Drain Current − Continuous (Note 1) − Pulsed (Note 2)	 I_D I_{DM}	 0.17 0.68	Adc

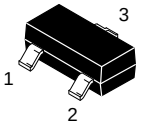
Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

THERMAL CHARACTERISTICS

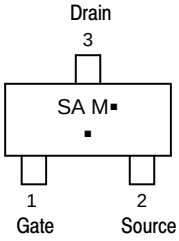
Characteristic	Symbol	Max	Unit
Total Device Dissipation FR−5 Board (Note 3) T_A = 25°C Derate above 25°C	P_D	 225 1.8	 mW mW/°C
Thermal Resistance, Junction−to−Ambient	$R_{\theta JA}$	556	°C/W
Junction and Storage Temperature	T_J, T_{stg}	−55 to +150	°C

1. The Power Dissipation of the package may result in a lower continuous drain current.
2. Pulse Width ≤ 300 μs, Duty Cycle ≤ 2.0%.
3. FR−5 = 1.0 × 0.75 × 0.062 in.

MARKING DIAGRAM & PIN ASSIGNMENT



SOT−23
CASE 318
STYLE 21



SA = Device Code
M = Date Code
▪ = Pb−Free Package

(*Note: Microdot may be in either location)

*Date Code orientation and/or position may vary depending upon manufacturing location.

ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 2 of this data sheet.

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted)

Characteristic	Symbol	Min	Typ	Max	Unit
OFF CHARACTERISTICS					
Drain−Source Breakdown Voltage (V_{GS} = 0, I_D = 250 μAdc)	$V_{(BR)DSS}$	100	−	−	Vdc
Zero Gate Voltage Drain Current (V_{GS} = 0, V_{DS} = 100 Vdc) T_J = 25°C T_J = 125°C	I_{DSS}	 − −	 − −	 15 60	μAdc
Gate−Body Leakage Current (V_{GS} = 20 Vdc, V_{DS} = 0)	I_{GSS}	−	−	50	nAdc
ON CHARACTERISTICS (Note 4)					
Gate Threshold Voltage (V_{DS} = V_{GS}, I_D = 1.0 mAdc)	$V_{GS(th)}$	1.6	−	2.6	Vdc
Static Drain−Source On−Resistance (V_{GS} = 10 Vdc, I_D = 100 mAdc)	$r_{DS(on)}$	−	−	6.0	Ω
Forward Transconductance (V_{DS} = 25 Vdc, I_D = 100 mAdc)	g_{fs}	80	−	−	mmhos
DYNAMIC CHARACTERISTICS					
Input Capacitance (V_{DS} = 25 Vdc, V_{GS} = 0, f = 1.0 MHz)	C_{iss}	−	20	−	pF
Output Capacitance (V_{DS} = 25 Vdc, V_{GS} = 0, f = 1.0 MHz)	C_{oss}	−	9.0	−	pF
Reverse Transfer Capacitance (V_{DS} = 25 Vdc, V_{GS} = 0, f = 1.0 MHz)	C_{rss}	−	4.0	−	pF
SWITCHING CHARACTERISTICS[4]					
Turn−On Delay Time (V_{CC} = 30 Vdc, I_C = 0.28 Adc, V_{GS} = 10 Vdc, R_{GS} = 50 Ω)	$t_{d(on)}$	−	20	−	ns
Turn−Off Delay Time	$t_{d(off)}$	−	40	−	ns
REVERSE DIODE					
Diode Forward On−Voltage (I_D = 0.34 Adc, V_{GS} = 0 Vdc)	V_{SD}	−	−	1.3	V

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

4. Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 2.0%.

ORDERING INFORMATION

Device	Package	Shipping†
BSS123LT1G	SOT−23 (Pb−Free)	3000 / Tape & Reel
BSS123LT3G	SOT−23 (Pb−Free)	10000 / Tape & Reel
BVSS123LT1G*	SOT−23 (Pb−Free)	3000 / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

*BVSS Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC−Q101 Qualified and PPAP Capable.

TYPICAL ELECTRICAL CHARACTERISTICS

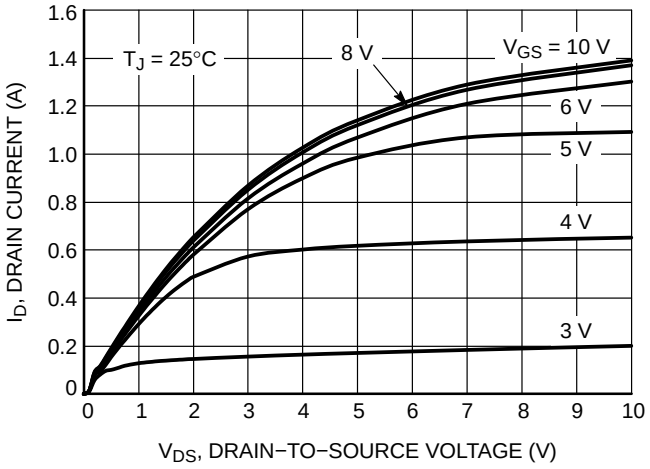


Figure 1. On−Region Characteristics

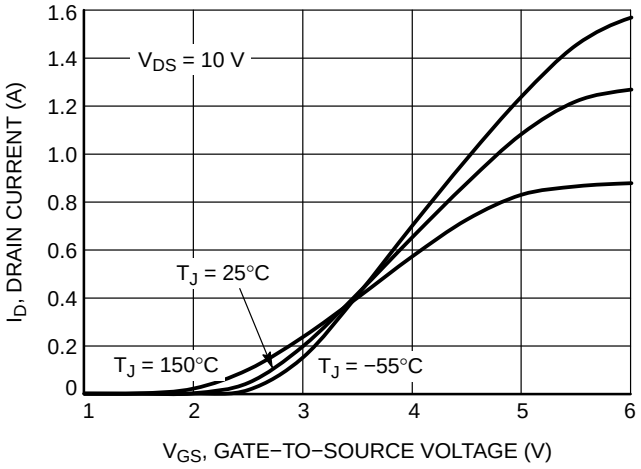


Figure 2. Transfer Characteristics

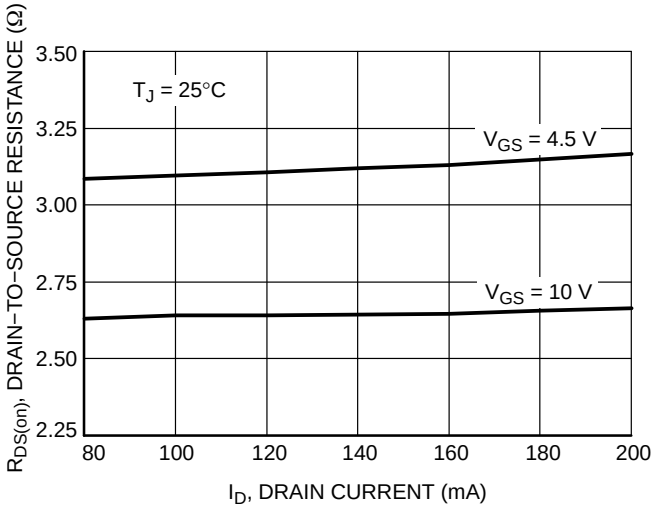


Figure 3. On−Resistance vs. Drain Current and Gate Voltage

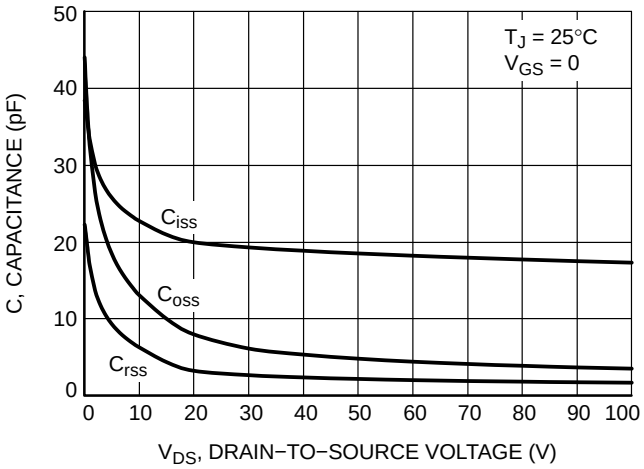


Figure 4. Capacitance Variation

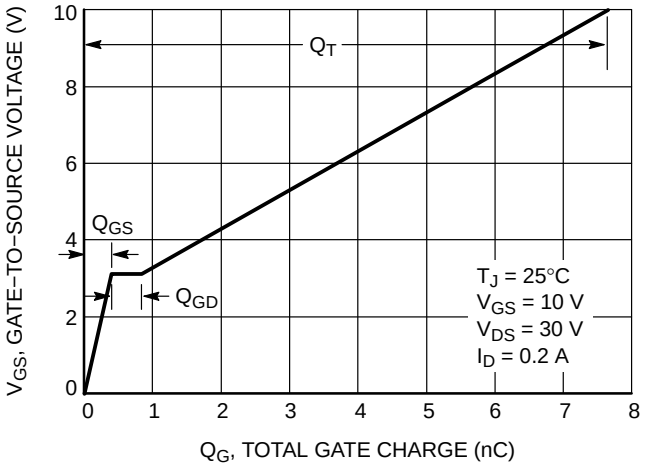


Figure 5. Gate−to−Source and Drain−to−Source Voltage vs. Total Charge

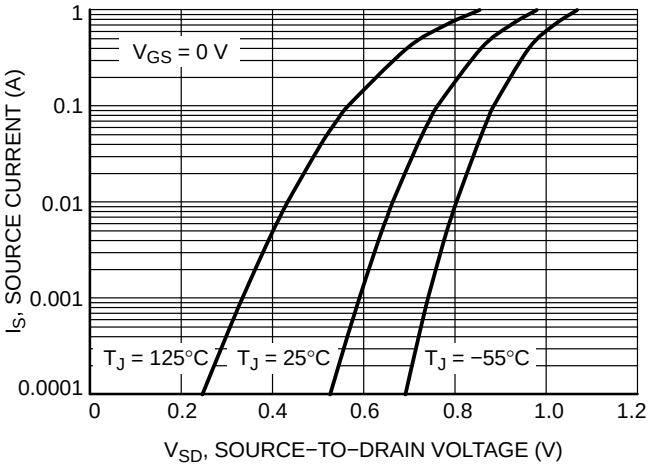


Figure 6. Diode Forward Voltage vs. Current

TYPICAL ELECTRICAL CHARACTERISTICS

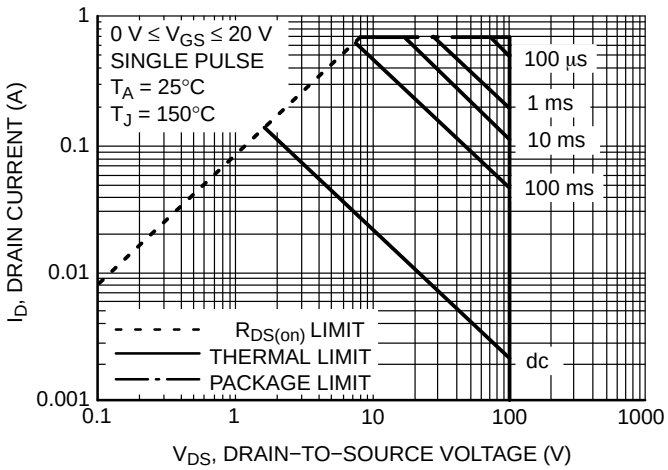


Figure 7. Maximum Rated Forward Biased Safe Operating Area

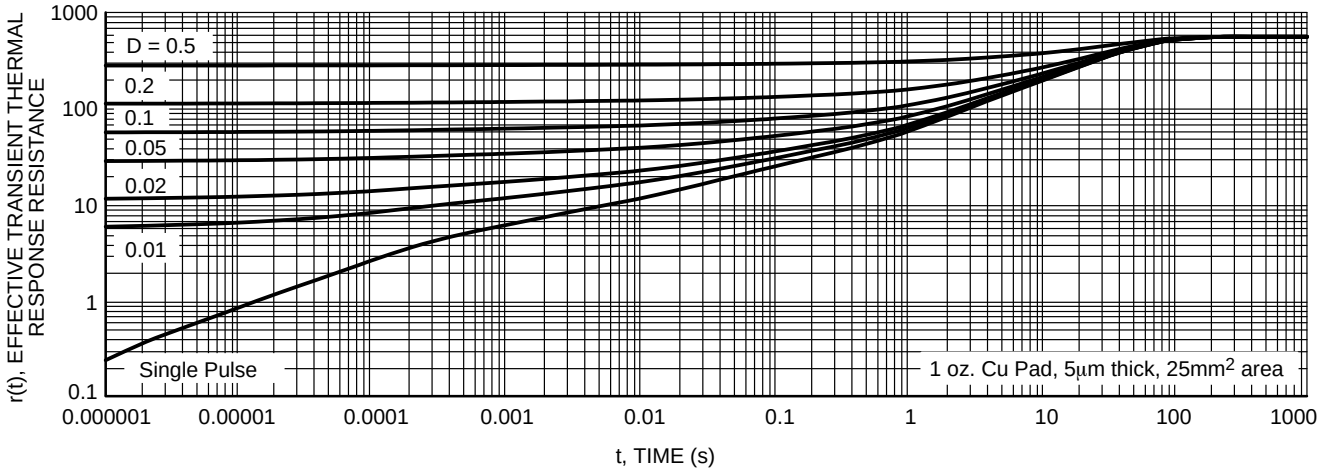
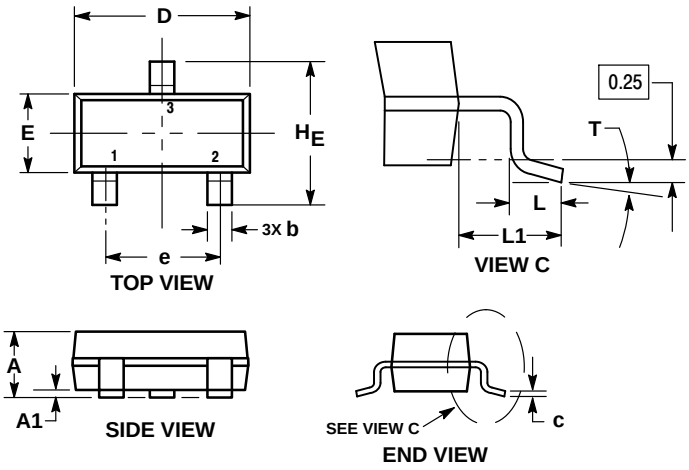


Figure 8. Thermal Response

PACKAGE DIMENSIONS

SOT−23 (TO−236)
CASE 318−08
ISSUE AR

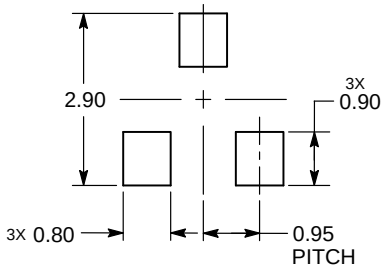


NOTES:
1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
2. CONTROLLING DIMENSION: MILLIMETERS.
3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF THE BASE MATERIAL.
4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS.

	MILLIMETERS			INCHES		
DIM	MIN	NOM	MAX	MIN	NOM	MAX
A	0.89	1.00	1.11	0.035	0.039	0.044
A1	0.01	0.06	0.10	0.000	0.002	0.004
b	0.37	0.44	0.50	0.015	0.017	0.020
c	0.08	0.14	0.20	0.003	0.006	0.008
D	2.80	2.90	3.04	0.110	0.114	0.120
E	1.20	1.30	1.40	0.047	0.051	0.055
e	1.78	1.90	2.04	0.070	0.075	0.080
L	0.30	0.43	0.55	0.012	0.017	0.022
L1	0.35	0.54	0.69	0.014	0.021	0.027
H_E	2.10	2.40	2.64	0.083	0.094	0.104
T	0°	−−−	10°	0°	−−−	10°

STYLE 21:
PIN 1. GATE
2. SOURCE
3. DRAIN

RECOMMENDED SOLDERING FOOTPRINT*



DIMENSIONS: MILLIMETERS

*For additional information on our Pb−Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

PUBLICATION ORDERING INFORMATION

LITERATURE FULFILLMENT:
Literature Distribution Center for ON Semiconductor
19521 E. 32nd Pkwy, Aurora, Colorado 80011 USA
Phone: 303−675−2175 or 800−344−3860 Toll Free USA/Canada
Fax: 303−675−2176 or 800−344−3867 Toll Free USA/Canada
Email: orderlit@onsemi.com

N. American Technical Support: 800−282−9855 Toll Free USA/Canada
Europe, Middle East and Africa Technical Support:
Phone: 421 33 790 2910
Japan Customer Focus Center
Phone: 81−3−5817−1050

ON Semiconductor Website: **www.onsemi.com**

Order Literature: http://www.onsemi.com/orderlit

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